

AMENDMENTS TO THE SPECIFICATION

Page 2, first full paragraph:

C2
In the semiconductor device of the constitution as described above, conduction between both surfaces of the interposer is taken by forming through holes and then filling a conductive material, for example, by plating. However, steps of forming fine through holes and applying plating therein results in a technical difficulty and in that it requires application of ~~to apply~~ a relatively thick plating; however, this creates a ~~to bring about~~ a problem of increasing the cost.

Page 4, first full paragraph, line 6:

C3
A method of manufacturing a clad plate according to this invention is characterized by forming a clad plate by previously applying an activating treatment to a bonding surface of a copper foil and a nickel foil or nickel plating in a vacuum vessel, then laminating the copper foil and, the nickel foil or the nickel plating and cold press-bonding them at 0.1 t θ to 3% rolling reduction in which the activating treatment is conducted <1> in an inert gas atmosphere at an extremely low pressure of 1×10 to 1×10 Pa, <2> using the nickel plated copper foil material and the copper foil material as one electrode A having the bonding surfaces grounded to the earth, respectively, and conducting glow discharge by applying an AC

C3
Concl'd

current at 1 to 50 MHz between it and the other electrode B supported insulatively and <4> applying sputter etching, <3> with the area of the electrode exposed in plasmas caused by the glow discharge being 1/3 or less of the electrode B.

Page 7, next to last paragraph:

C4

Subsequently, they are cold press-bonded by a rolling unit 30 disposed in the vacuum vessel 29 and an interposer-forming clad plate 31 having a three layered structure for use in a semiconductor device is wound around a delivery roll 32.

Page 9, second full paragraph:

C5

Further, when three or more sets of delivery reels are disposed, copper foil material or nickel foil material are disposed to the reels and foil materials are simultaneously supplied from the three or more reels, a clad plate of a multi-layered structure can be manufactured by press-bonding only ~~for~~ once.

Page 11, last paragraph:

C6

In the interposer for use in the semiconductor device according to this invention, since the interposer-forming clad plate for use in the semiconductor device as described above is etched selectively, to former connection bumps with semiconductor chip and the wiring layer and conduction of the interposer along the direction of the thickness is taken by way of the columnar conductor formed by etching, the interposer for use in the semiconductor

C6
Concl'd

device capable of coping with the small sized semiconductor device can be manufactured efficiently at a reduced cost. Further, since connection between the semiconductor chip and the wiring layer is conducted through the semiconductor chip connection bumps by using anisotropically conductive adhesives containing conductive particles, there is no requirement for forming the bump on the semiconductor chip and the cost for the semiconductor device can be reduced.

Page 12, last paragraph:

C7

In the method of manufacturing the interposer-forming clad plate for use in the semiconductor device according to this invention, since the clad plate is formed by previously applying the activating treatment to the bonded surfaces of the copper foil and the nickel plating in the vacuum vessel, then laminating the copper foil and the nickel plating and cold press-bonding them at a rolling reduction of 0.1 to 3% in a vacuum vessel, the planarity at the bonded boundary can be maintained by suppressing the stress at the bonding boundary, and since the heat treatment for the restoration of the workability is no more required and no alloy layer is formed at the boundary, the interposer-forming clad plate for use in the semiconductor device of excellent selective etching property can be manufactured.
